

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \max}$	$I_D \max$ $T_A = +25^\circ\text{C}$
60V	7.5Ω @ $V_{GS} = 5V$	210mA

## Features and Benefits

- N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q101) for High Reliability.**
- <https://www.diodes.com/quality/product-definitions/>

## Description and Applications

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

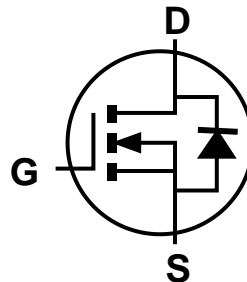
- Motor Control
- Power Management Functions

## Mechanical Data

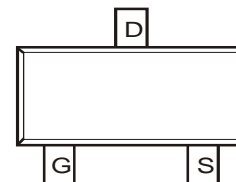
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 Ⓜ3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)



Top View



Equivalent Circuit



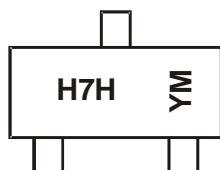
Top View

## Ordering Information (Note 3)

Part Number	Case	Packaging
2N7002H-7	SOT23	3,000/Tape & Reel
2N7002H-13	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



H7H = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: B = 2014)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021
Code	B	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

## Maximum Ratings (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		$V_{DSS}$	60	V
Gate-Source Voltage		$V_{GSS}$	Continuous	$\pm 20$
			Pulsed	$\pm 40$
Continuous Drain Current (Note 5) $V_{GS} = 10\text{V}$	Steady State	$I_D$	$T_A = +25^\circ\text{C}$	170
			$T_A = +85^\circ\text{C}$	120
			$T_A = +100^\circ\text{C}$	105
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$I_D$	$T_A = +25^\circ\text{C}$	210
			$T_A = +85^\circ\text{C}$	150
			$T_A = +100^\circ\text{C}$	135
Maximum Body Diode Forward Current (Note 6)		$I_S$	Continuous	0.5
			Pulsed	2
Pulsed Drain Current (10 $\mu\text{s}$ pulse, duty cycle = 1%)		$I_{DM}$	500	mA

## Thermal Characteristics (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	$P_D$	370	mW
	(Note 6)		510	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	341	$^\circ\text{C/W}$
	(Note 6)		249	
Operating and Storage Temperature Range		$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	2.0	—	3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	3.0	7.5	Ω	V <sub>GS</sub> = 5.0V, I <sub>D</sub> = 0.05A
Diode Forward Voltage	V <sub>SD</sub>	—	0.78	1.5	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>ISS</sub>	—	26	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>OSS</sub>	—	2.8	—	pF	
Reverse Transfer Capacitance	C <sub>rSS</sub>	—	2.1	—	pF	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	352	—	pC	V <sub>DS</sub> = 10V, I <sub>D</sub> = 250mA
Gate-Source Charge	Q <sub>gs</sub>	—	203	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	123	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	3.7	—	ns	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.2A, R <sub>L</sub> = 150Ω, V <sub>GEN</sub> = 10V, R <sub>GEN</sub> = 25Ω
Turn-On Rise Time	t <sub>r</sub>	—	2.9	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	8.4	—		
Turn-Off Fall Time	t <sub>f</sub>	—	4.7	—		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	—	9.3	—	ns	I <sub>S</sub> = 0.5A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	—	3.5	—	nC	I <sub>S</sub> = 0.5A, dI/dt = 100A/μs

- Notes:
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
  6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.

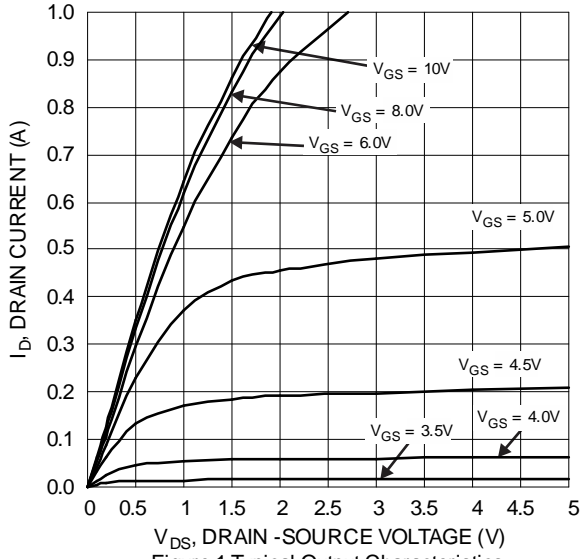


Figure 1 Typical Output Characteristics

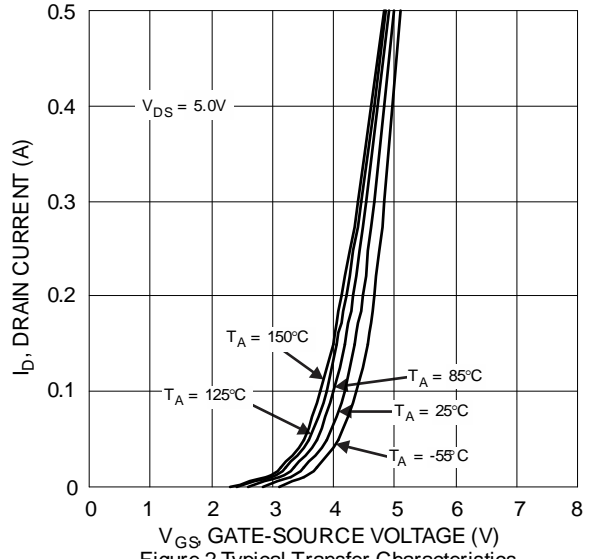


Figure 2 Typical Transfer Characteristics

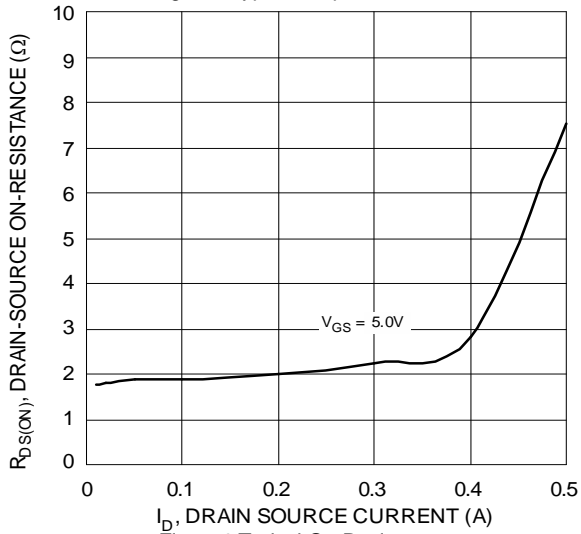


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

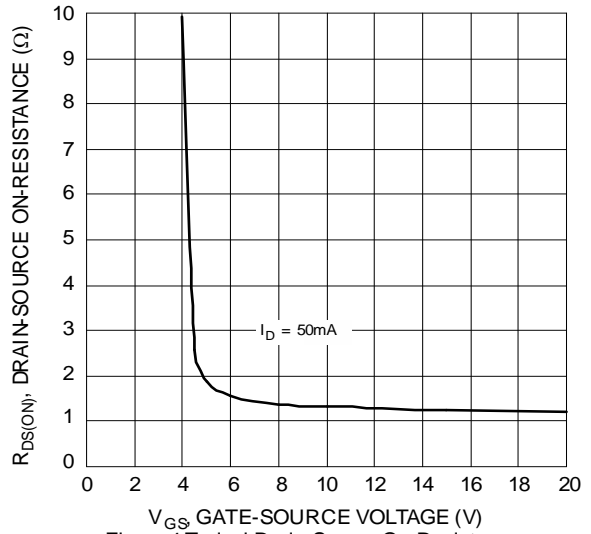


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

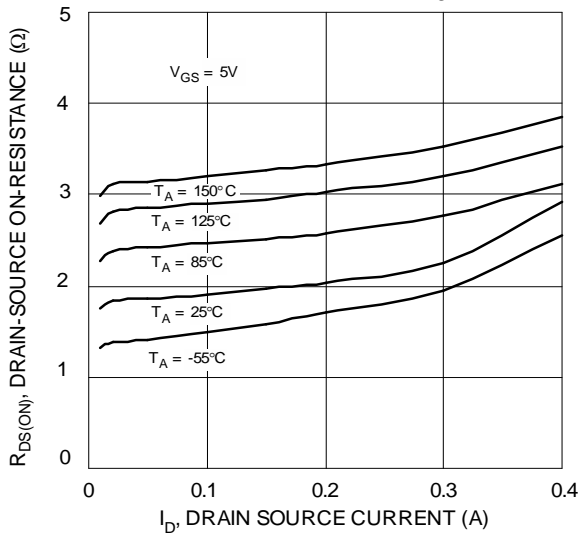


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

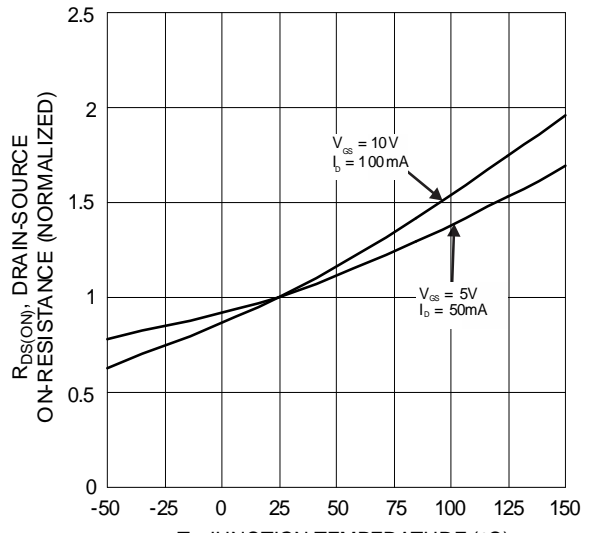


Figure 6 On-Resistance Variation with Temperature

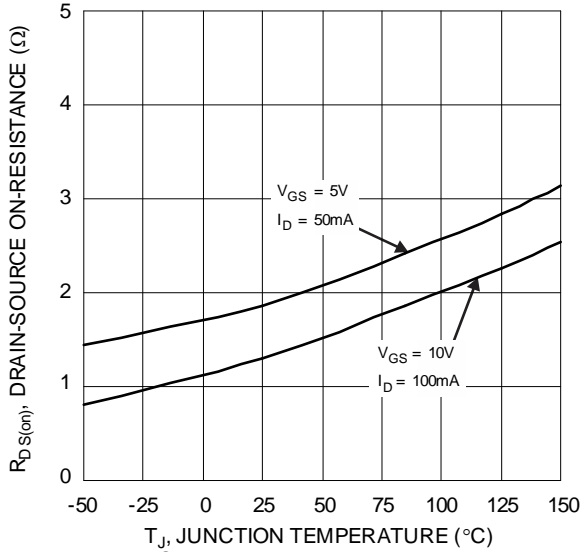


Figure 7 On-Resistance Variation with Temperature

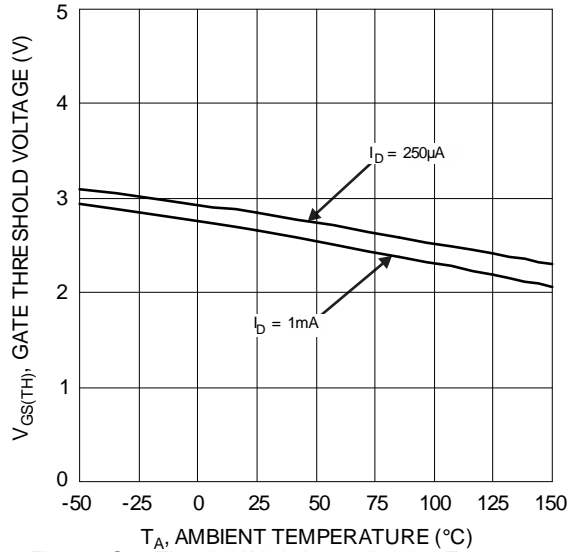


Figure 8 Gate Threshold Variation vs. Ambient Temperature

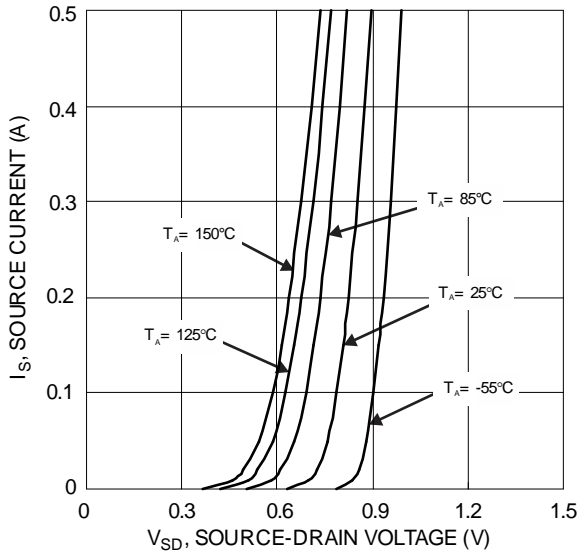


Figure 9 Diode Forward Voltage vs. Current

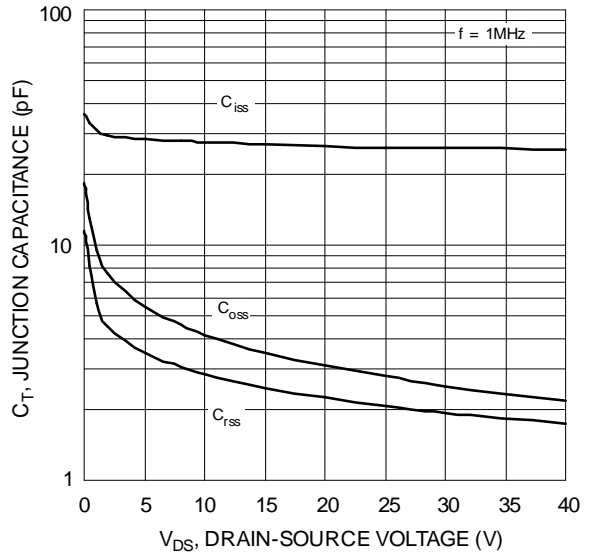


Figure 10 Typical Junction Capacitance

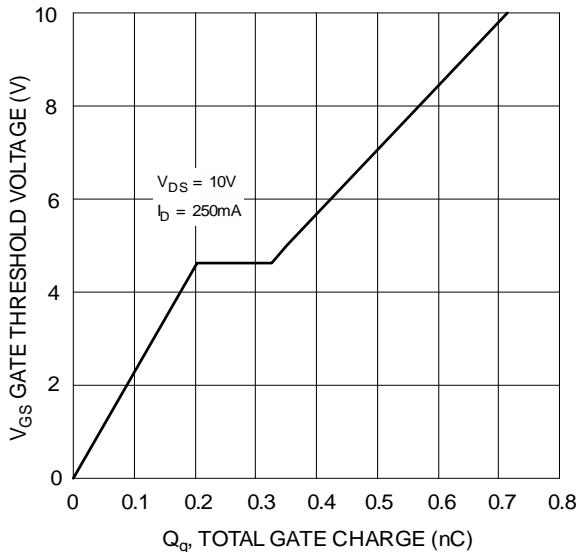


Figure 11 Gate Charge

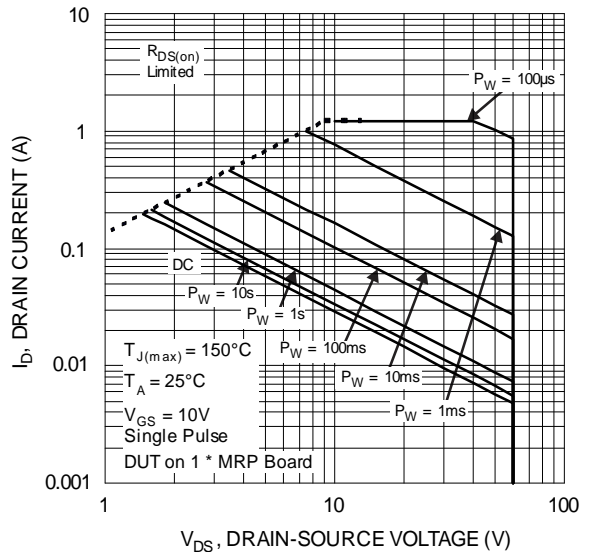
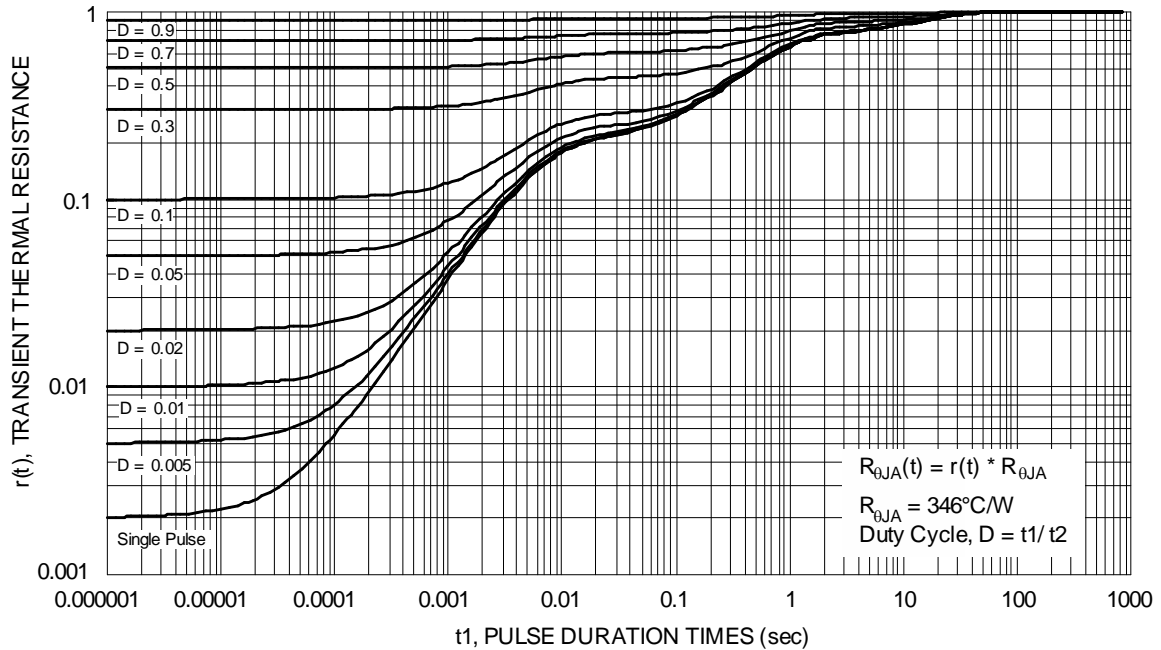
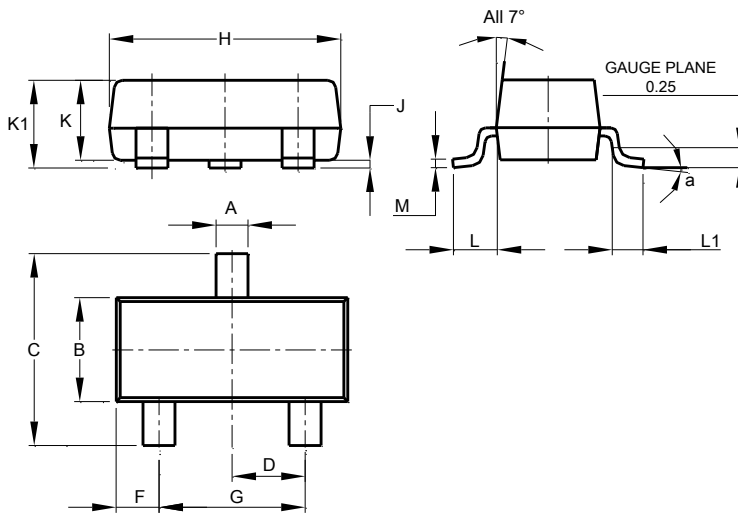


Figure 12 SOA, Safe Operation Area



**Package Outline Dimensions**

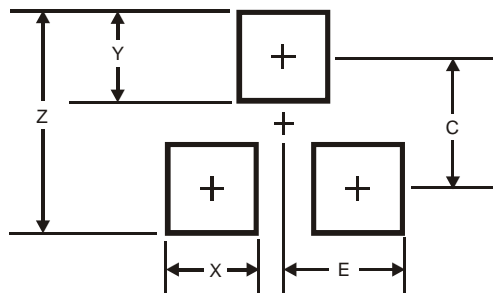
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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